

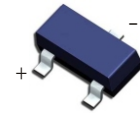
SMD Switching Diode



SMD Diodes Specialist

CDST19-G/20-G/21-G

High Speed
RoHS Device



Features

- Fast switching diode.
- Surface mount package ideally for automatic insertion.
- For general purpose switching applications.
- High conductance.

Mechanical data

Case: SOT-23

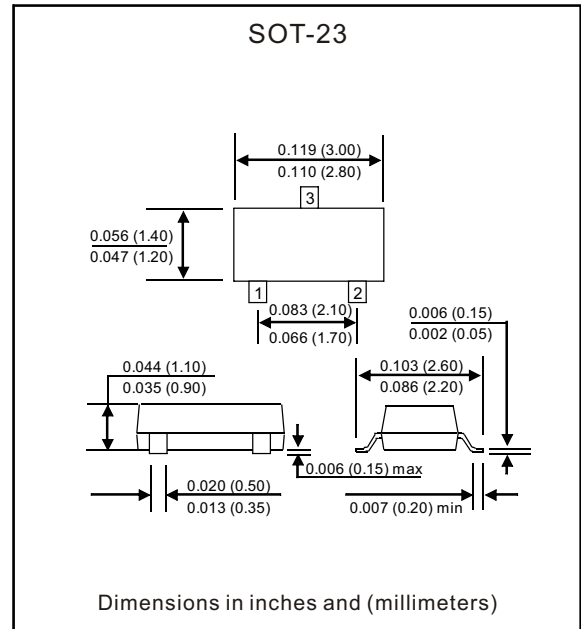
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

Weight: 0.008 gram.

Marking: CDST19-G JP

CDST20-G JR

CDST21-G JS



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Symbol	CDST19-G	CDST20-G	CDST21-G	Unit
Non-Repetitive peak reverse voltage	V_{RM}	100	150	200	V
DC blocking voltage	V_R	100	150	200	V
Average rectified output current	I_o	200			mA
Power dissipation	P_D	250			mW
Thermal resistance-Junction to ambient air	$R_{\theta JA}$	500			°C/W
Junction temperature	T_J	150			°C
Storage temperature range	T_{STG}	-65 ~ +150			°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V_{BR}	$I_R=100\mu A$	100 150 200		V
Reverse leakage current	I_R	$V_R=100V$ $V_R=150V$ $V_R=200V$		0.1	UA
Forward voltage	V_F	$I_F=100mA$ $I_F=200mA$		1 1.25	V
Junction capacitance	C_J	$V_R=0V, f=1MHz$		5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=30mA, I_{rr}=0.1 \times I_R$		50	nS

Characteristic Curves (CDST19-G/20-G/21-G)

Fig. 1 - Forward Characteristics

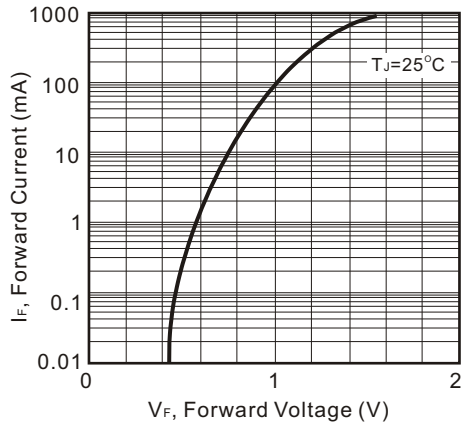


Fig. 2 - Leakage Current vs Junction Temperature

